Nch 500V 11A Power MOSFET

V _{DSS}	500V
R _{DS(on)} (Max.)	0.52Ω
I _D	±11A
P _D	59W

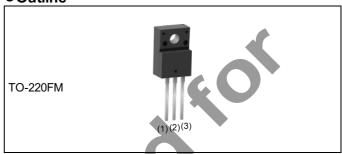
Features

- 1) Fast reverse recovery time(t_{rr}).
- 2) Low on-resistance.
- 3) Fast switching speed.
- 4) Gate-source voltage (V_{GSS}) guaranteed to be ±30V.
- 5) Drive circuits can be simple.
- 6) Parallel use is easy.

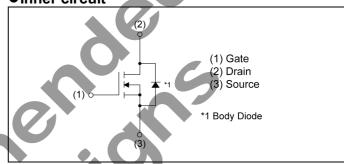
Application

Switching

Outline



•Inner circuit



Packaging specifications

6	Packing	Bulk
0	Reel size (mm)	1
Time	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	R5011FNX

● **Absolute maximum ratings** (T_a = 25°C ,unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	500	V
Continuous drain aurrant	T _C = 25°C	I _D *1	±11	А
Continuous drain current	T _C = 100°C	I _D *1	±5.4	Α
Pulsed drain current		l _{DP} *2	±44	Α
Gate - Source voltage	V_{GSS}	±30	V	
Avalanche current, repetitive	l _{AR} *3	5.5	Α	
Avalanche energy, single pulse		$E_{AS}^{}^{*3}}$	8.1	mJ
Avalanche energy, repetitive		E _{AR} *5	3.5	mJ
Power dissipation (T _C = 25°C)	P _D *4	59	W	
Junction temperature	T _j	150	°C	
Operating junction and storage tem	T _{stg}	-55 ~ +150	°C	

● Absolute maximum ratings (T_a = 25°C)

Parameter	Symbol	Conditions	Values	Unit
Reverse diode dv/dt	dv/dt	-	15	V/ns
Drain - Source voltage slope	dv/dt	$V_{DS} = 400V, T_j = 125$ °C	50	V/ns

●Thermal resistance

Doromotor	Cumb ol	Values			l lait	
Parameter	Symbol	Min.	Тур.	Max.	Unit	
Thermal resistance, junction - case	R _{thJC}		-	2.10	°C/W	
Thermal resistance, junction - ambient	R _{thJA}	-	-	70	°C/W	
Soldering temperature, wavesoldering for 10s	T _{sold}	_	C	265	°C	

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol Conditions		Values			Unit	
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic	
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V$, $I_D = 1mA$	500	ı	-	V	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 500V, V_{GS} = 0V$ $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$	-	1 -	100 10000	μA	
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	±100	nA	
Gate threshold voltage	V _{GS(th)}	V _{DS} = 10V, I _D = 1mA	2.0	-	4.0	V	
Static drain - source on - state resistance	R _{DS(on)} *6	$V_{GS} = 10V, I_D = 5.5A$ $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$	1 1	0.40 0.85	0.52	Ω	
Gate resistance	R_{G}	f =1MHz, open drain	-	8.8	-	Ω	

●Electrical characteristics (T_a = 25°C)

Davanastan	Cy made al	Conditions		I limit		
Parameter	Symbol	Conditions	Min.	Min. Typ. Max		Unit
Forward Transfer Admittance	Y _{fs} *6	V _{DS} = 10V, I _D = 5.5A	4.5	-	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	950	(-)	
Output capacitance	C _{oss}	V _{DS} = 25V	-	580	1	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	30	-	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V	7	50.8	-	
Effective output capacitance, time related	C _{o(tr)}	V _{DS} = 0V to 400V)	51.2	-	pF
Turn - on delay time	t _{d(on)} *6	V _{DD} ≈ 250V,V _{GS} = 10V	-	26	-	
Rise time	t _r *6	I _D = 5.5A	(-)	28	-	20
Turn - off delay time	t _{d(off)} *6	R _L ≈ 45.5Ω		75	-	ns
Fall time	t _f *6	R _G = 10Ω	-	30	-	

• Gate charge characteristics $(T_a = 25^{\circ}C)$

Parameter	Symbol Conditions		Values			l leit
Parameter	Symbol	Conditions		Тур.	Max.	Unit
Total gate charge	Q _g *6	V _{DD} ≃ 250V,	-	30	-	
Gate - Source charge	Q _{gs} *6	I _D = 11A,	-	7	-	nC
Gate - Drain charge	Q _{gd} *6	V _{GS} = 10V	-	12	-	
Gate plateau voltage	V _(plateau)	V _{DD} = 250V, I _D = 11A	-	5.9	-	V

^{*1} Limited only by maximum channel temperature allowed.

*6 Pulsed

^{*2} Pw ≤ 10µs, Duty cycle ≤ 1%

^{*3} L \doteqdot 500 μ H, V_{DD}=50V, R_G=25 Ω , STARTING T $_{j}$ =25 $^{\circ}$ C

^{*4} T_C=25°C

^{*5} L $\stackrel{.}{=}$ 500 μ H, V_{DD}=50V, R_G=25 Ω , STARTING T $_{j}$ =25 $^{\circ}$ C, f=10kHz

● Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions		Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous forward current	I _S *1	T = 25°C	-	-	11	А
Pulse forward current	l _{SP} *2	T _c = 25°C	-	-	44	А
Forward voltage	V _{SD} *6	V _{GS} = 0V, I _S = 11A	-	-	1.5	V
Reverse recovery time	t _{rr} *6		55	85	115	ns
Reverse recovery charge	Q _{rr} *6	I _S = 11A, V _{GS} =0V di/dt = 100A/μs		0.33	-	μC
Peak reverse recovery current	I _{mm} *6	1007 Upo	V	7.4	-	Α

● Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R _{th1}	0.178		C _{th1}	0.00269	
R _{th2}	0.853	K/W	C _{th2}	0.0273	Ws/K
R _{th3}	2.36		C _{th3}	0.463	

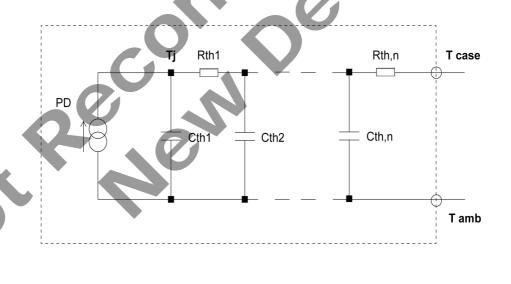


Fig.1 Power Dissipation Derating Curve

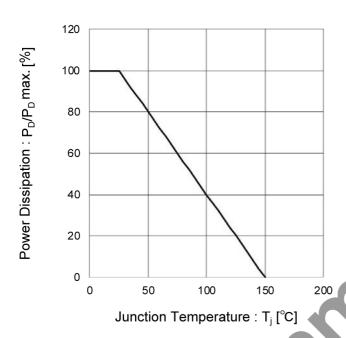


Fig.2 Maximum Safe Operating Area

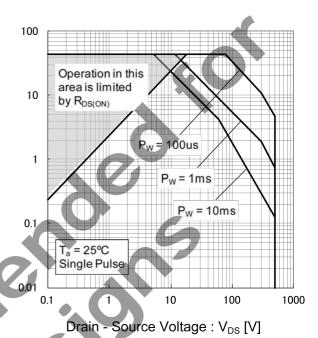


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

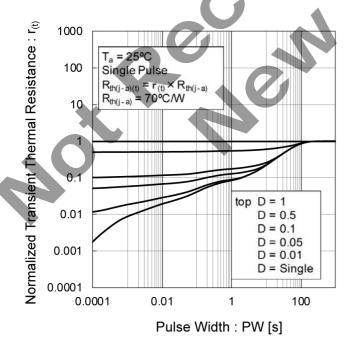


Fig.4 Avalanche Energy Derating
Curve vs. Junction Temperature

Drain Current: I_D [A]

Fig.5 Typical Output Characteristics(I)

20 Ta= 25°C 10V Pulsed 8.0V 7.0V 15 Drain Current : I_D [A] 6.0V 6.5V 10 5.5V 5 5.0V V_{GS}= 4.5V 0 30 0 10 20 40 Drain - Source Voltage: VDS [V]

Fig.6 Typical Output Characteristics(II)

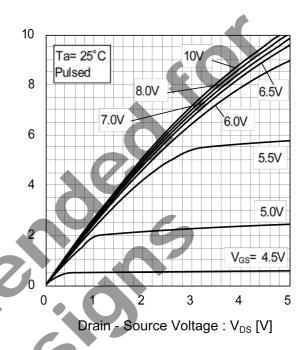


Fig.7 Tj = 150°C Typical Output Characteristics (I)

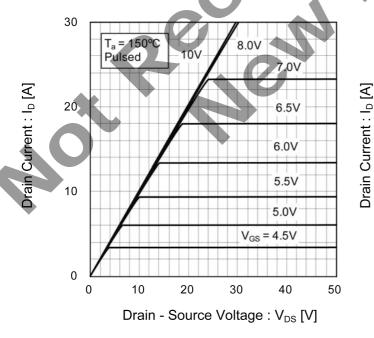
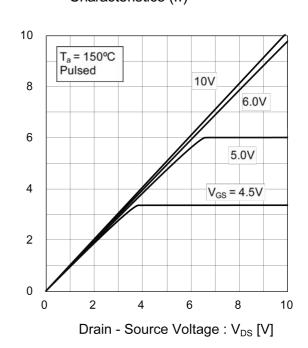


Fig.8 Tj = 150°C Typical Output Characteristics (II)



Drain Current : I_D [A]

Fig.9 Breakdown Voltage vs.
Junction Temperature

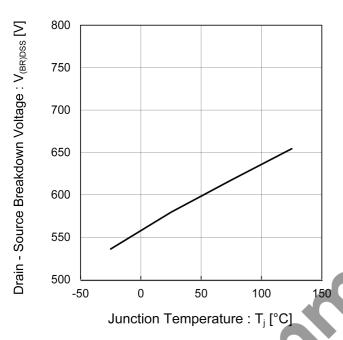


Fig.10 Typical Transfer Characteristics

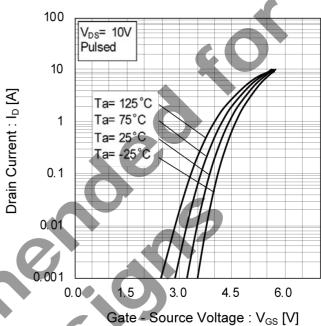


Fig.11 Gate Threshold Voltage vs. Junction Temperature

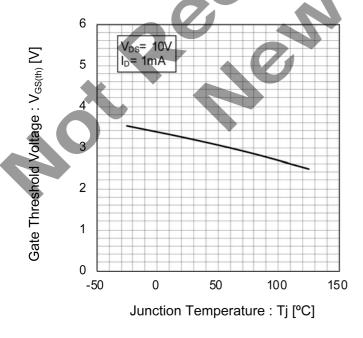


Fig.12 Forward Transfer Admittance vs.
Drain Current

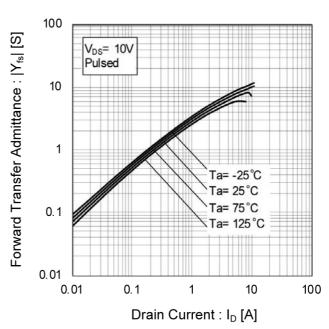


Fig.13 Static Drain - Source On - State Resistance vs. Gate Source Voltage

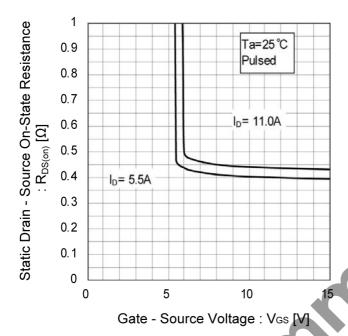


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature

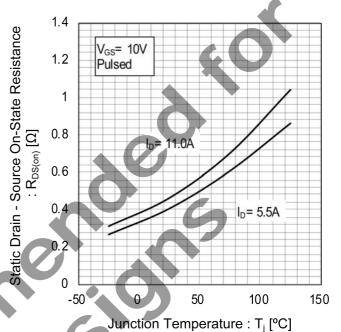


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current



Fig.16 Typical Capacitance vs.
Drain - Source Voltage

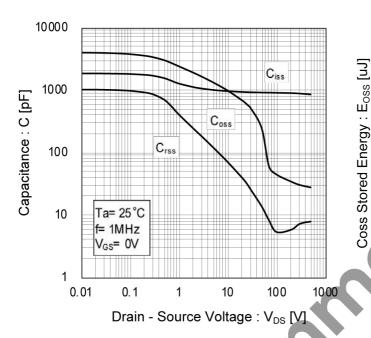


Fig.17 Coss Stored Energy

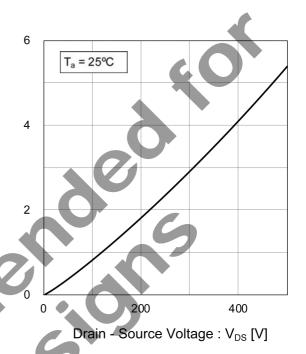


Fig.18 Switching Characteristics

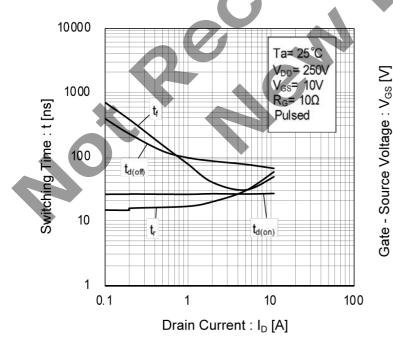


Fig.19 Dynamic Input Characteristics

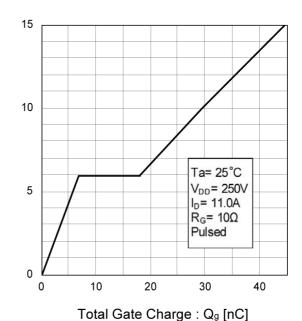


Fig.20 Inverse Diode Forward Current vs. Source - Drain Voltage

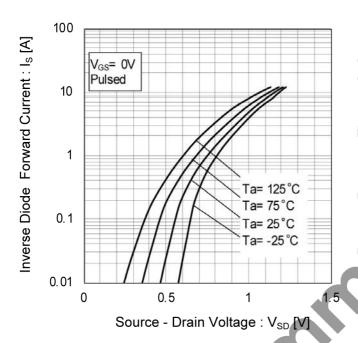
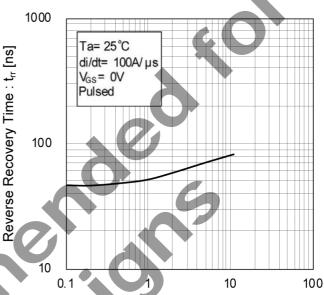


Fig.21 Reverse Recovery Time vs.
Inverse Diode Forward Current



Inverse Diode Forward Current: Is [A]



Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

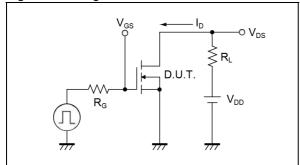


Fig.2-1 Gate Charge Measurement Circuit

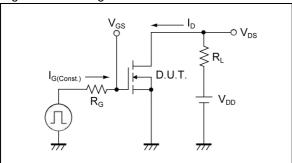


Fig.3-1 Avalanche Measurement Circuit

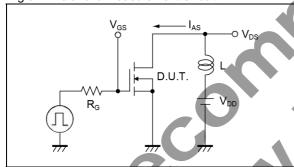


Fig.4-1 dv/dt Measurement Circuit

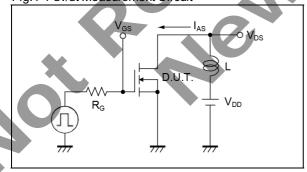


Fig.5-1 dv/dt Measurement Circuit

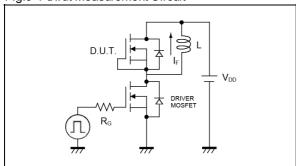


Fig.1-2 Switching Waveforms

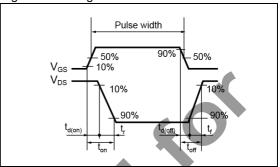


Fig.2-2 Gate Charge Waveform

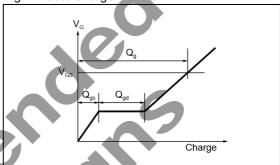


Fig.3-2 Avalanche Waveform

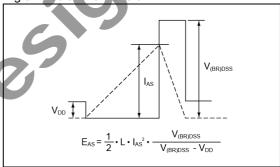


Fig.4-2 dv/dt Waveform

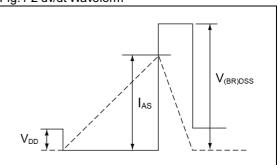
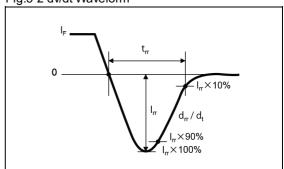
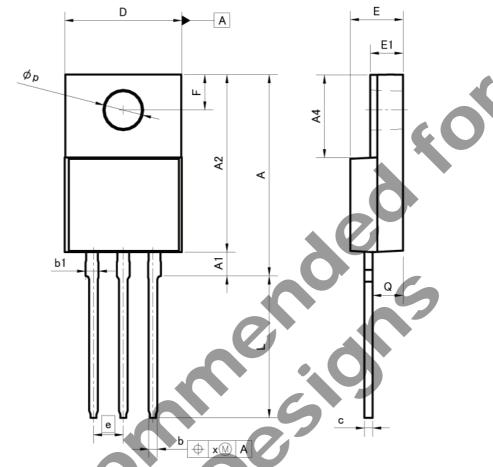


Fig.5-2 dv/dt Waveform



Dimensions





DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
A	16.60	17.60	0.654	0.693	
A1	1.80	2.20	0.071	0.087	
A2	14.80	15.40	0.583	0.606	
A4	6.80	7.20	0.268	0.283	
b	0.70	0.90	0.028	0.035	
b1	1.10	1.50	0.043	0.059	
С	0.70	0.85	0.028	0.033	
D	9.90	10.30	0.390	0.406	
E	4.40	4.80	0.173	0.189	
е	2.	54	0.100		
E1	2.70	3.00	0.106	0.118	
F	2.80	3.20	0.110	0.126	
L	11.50	12.50	0.453	0.492	
р	3.00	3.40	0.118	0.134	
Q	2.10	3.10	0.083	0.122	
х	8 — 8	0.38	<u>20</u> %	0.015	

Dimension in mm/inches



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 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power, exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

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 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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